



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SB85 SILICON SCHOTTKY DETECTING DIODE REVERSE VOLTAGE: 50V FORWARD CURRENT: 150mA

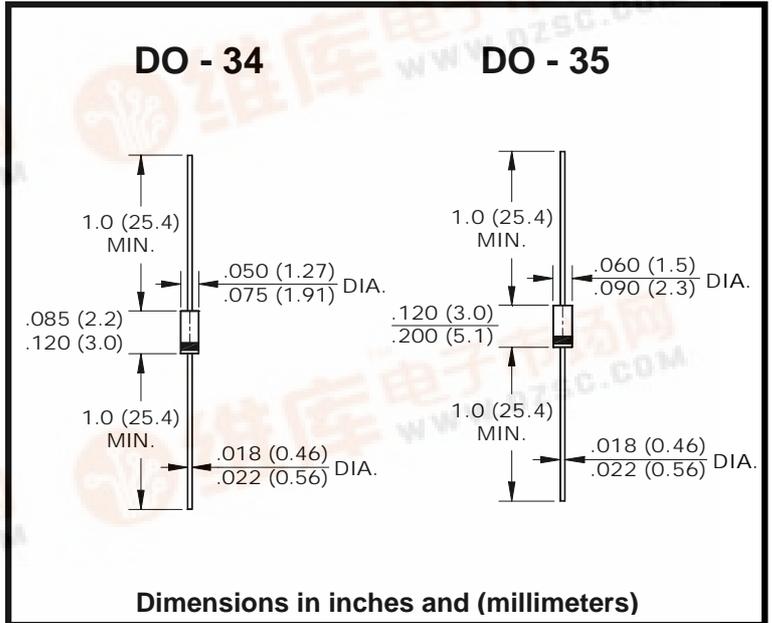
TECHNICAL SPECIFICATION

FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
250°C/10S/9.5mm lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE		UNITS
		Typ.	Max.	
Reverse Voltage	V_R		50	V
Forward Current (peak)	I_{FM}		150	mA
Forward Current (D.C.)	I_F		30	mA
Forward Voltage (D.C.)	$I_F=10mA$	V_{F1}	0.4	V
	$I_F=100mA$	V_{F2}	0.8	V
Reverse Current ($V_R=30V$)	I_R		3	μA
Capacitance (Note 1)	C_t	6		pF
Detection Effectiveness (Note 2)	η	60%		
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~+125		°C

Notes:

1. $V_R=10V, f=1MHz$
2. $V_m=3V(\text{peak}), f=30MHz, R_L=3.9K\Omega, C_t=10pF.$

